



Microsemi Corp.

The diode experts

**1N4099 thru
1N4135
and
1N4614 thru
1N4627
DO-7**

SCOTTSDALE, AZ.
For more information call:
(602) 941-6300

FEATURES

- ZENER VOLTAGE 1.8V to 100V
- ALL HAVE JAN, JANTX and JANTXV - 1 QUALIFICATIONS TO MIL-S-19500/435
- LOW NOISE
- LOW REVERSE LEAKAGE

MAXIMUM RATINGS

Junction and Storage Temperatures: -65°C to +200°C

DC Power Dissipation: 400 mW

Power Derating: 2.66 mW/°C above 50°C in DO-7

Forward Voltage @ 200 mA: 1.0 Volts 1N4099 - 1N4135

@ 100 mA: 1.0 Volts 1N4614 - 1N4627

**SILICON
400 mW
LOW NOISE
ZENER DIODES**

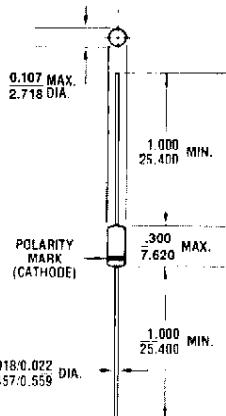


FIGURE 1
All dimensions in
INCH
m.m.

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed glass case, DO-7.

FINISH: All external surfaces are corrosion resistant and leads solderable.

THERMAL RESISTANCE: 300°C/W (Typical) junction to lead at 0.375-inches from body on DO-7.

POLARITY: Diode to be operated with the banded end positive with respect to the opposite end.

WEIGHT: 0.2 grams.

MOUNTING POSITION: Any.

* ELECTRICAL CHARACTERISTICS @ 25°C

JEDEC TYPE NO.	NOMINAL ZENER VOLTAGE $V_Z = 1/2 T$ (Note 1)	ZENER TEST CURRENT I_ZT	MAXIMUM ZENER IMPEDANCE Z_{ZT} (Note 2)	MAXIMUM REVERSE CURR/HF VI $I_{ZS} = 1/2 V_R$	MAXIMUM NOISE POWER/ I_ZT $P_N = 1/2 V_R$	MAXIMUM ZENER CURRENT I_{ZM} (Note 3)	MAXIMUM TEMP. COEFF. OF ZENER VOLTAGE ΔV_Z
	VOLTS	µA	OHMS	µA	VOLTS	µV/√Hz	mA
1N4614	1.8	250	1200	7.5	1	1	-0.075
1N4615	2.0	250	1200	5.0	1	1	-0.075
1N4616	2.2	250	1200	4.0	1	1	-0.075
1N4617	2.4	250	1400	3.0	1	1	-0.075
1N4618	2.7	250	1500	1.0	1	1	-0.075
1N4619	3.0	250	1600	0.8	1	1	-0.075
1N4620	3.3	250	1650	2.5	1.5	1	-0.075
1N4621	3.6	250	1700	2.5	2	1	-0.065
1N4622	3.9	250	1650	5.0	2	1	-0.060
1N4623	4.5	250	1600	4.0	2	1	-0.050
1N4624	4.7	250	1550	10.0	3	1	-0.050/0.020
1N4625	5.1	250	1500	1.0	3	2	-0.045/0.030
1N4626	5.6	250	1400	1.0	4	4	-0.020/0.040
1N4627	6.2	250	1200	1.0	5	5	-0.010/0.050
1N4628	6.8	250	200	10.0	5.17	40	55
1N4629	7.5	250	200	10.0	5.70	40	51
1N4630	8.2	250	200	10.0	6.24	40	56
1N4132	8.7	250	200	1.0	6.61	40	44
1N4133	9.1	250	200	1.0	6.92	40	42
1N4124	10	250	200	1.0	7.60	40	38
1N4105	11	250	200	.05	8.44	40	35
1N4106	12	250	200	.05	9.12	40	37
1N4107	13	250	200	.05	9.87	40	29
1N4108	14	250	200	.05	10.65	40	27
1N4109	15	250	100	.05	11.40	40	28
1N4110	16	250	100	.05	12.15	40	24
1N4111	17	250	100	.05	12.92	40	22
1N4112	18	250	100	.05	13.87	40	21
1N4113	19	250	100	.05	14.44	40	20
1N4114	20	250	150	.01	15.20	40	19
1N4115	22	250	150	.01	16.72	40	17
1N4116	24	250	150	.01	18.25	40	16
1N4117	25	250	150	.01	19.00	40	15
1N4118	27	250	150	.01	20.45	40	14
1N4119	28	250	200	.01	21.28	40	14
1N4120	30	250	200	.01	22.80	40	13
1N4121	33	250	200	.01	25.08	40	12
1N4122	36	250	200	.01	27.98	40	11
1N4123	39	250	200	.01	29.65	40	9.8
1N4124	43	250	75.9	.01	32.65	40	8.9
1N4125	47	250	250	.01	35.75	40	8.1
1N4126	51	250	300	.01	38.76	40	7.5
1N4127	56	250	300	.01	42.60	40	6.7
1N4128	60	250	400	.01	45.60	40	6.4
1N4129	62	250	600	.01	47.10	40	6.1
1N4130	68	250	700	.01	51.88	40	5.6
1N4131	70	250	700	.01	57.00	40	5.1
1N4132	82	250	800	.01	62.32	40	4.6
1N4133	87	250	1000	.01	66.12	40	4.4
1N4134	91	250	1200	.01	69.16	40	4.2
1N4135	100	250	1500	.01	76.00	40	3.8

* ESD-DFN® Registered Data.

1N4099 thru 1N4135, 1N4614 thru 1N4627 DO-7

Noise density, (N_D) is specified in microvolts-rms per square-root-hertz. Actual measurement is performed using a 1 KHz to 3 KHz frequency bandpass filter at a constant Zener test current (I_{ZT}) at 25°C ambient temperature. N_D is calculated from the formula.

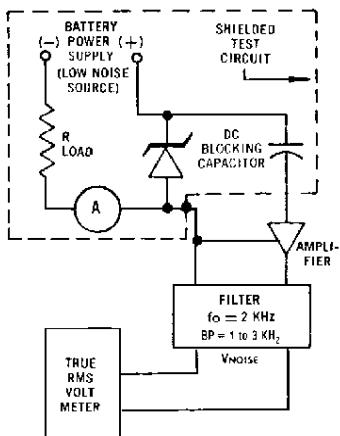


FIGURE 2 NOISE DENSITY MEASUREMENT CIRCUIT

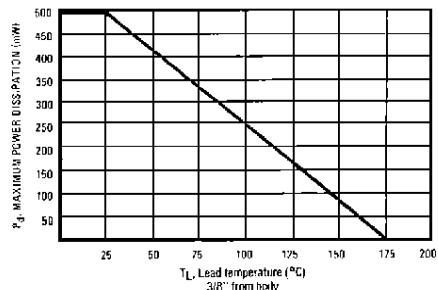


FIGURE 3 POWER DERATING CURVE

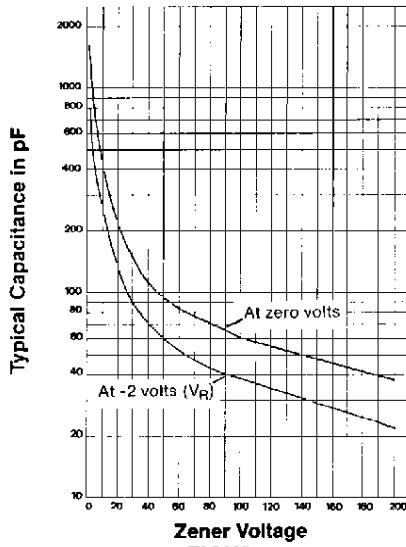


FIGURE 4
CAPACITANCE VS. ZENER VOLTAGE
(TYPICAL)

NOTE 1 The JEDEC type numbers shown with no suffix have a standard tolerance of $\pm 5\%$ on the nominal Zener voltage; suffix C is used to identify $\pm 2\%$; and suffix D is used to identify $\pm 1\%$ tolerance. V_Z is measured with the diode in thermal equilibrium in 25°C still air.

NOTE 2 Zener impedance is derived by superimposing on I_{ZT} , a 60 Hz rms a.c. current equal to 10% of I_{ZT} (25 μA a.c.).

NOTE 3 Based upon 400 mW maximum power dissipation at 25°C ambient temperature, allowance has been made for the higher voltage associated with operation at higher currents.